

EAST - [1.wsp:1]

File View Edit Tools Window Help

☐ Pending
☒ Active
 L1: (3776) com
 L2: (23) 1 and
☐ Failed
☐ Saved
☐ Favorites
☐ Tagged (0)

Search

DB: USPAT,USPGPUB,EPO,JPO,DERWENT,IBM,TOB ☐ Plink

Default operator: OR ☒ Highlight all fil terms initially

1 and first adj bit and second adj bit and third adj bit and fourth adj bit

☒ BRS term ☒ USR term ☐ Image ☐ Text ☐ HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
12	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5381367 A	19950110		Semiconductor memory device and an operating method of	365/189.01	365/189.03; 365/221;	
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5369647 A	19941129		Circuitry and method for testing a write state	714/736	365/201; 714/718	
14	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5289428 A	19940222		Semiconductor memory device	365/230.05	365/230.03; 365/230.09	
15	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4812918 A	19890314		Method and apparatus for scanning and digitizing	358/2.99	358/296; 358/476;	
16	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4789961 A	19881206		Computer memory back-up with automatic tape positioning	360/72.1	360/74.1	
17	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4525780 A	19850625		Data processing system having a memory using	711/163		
18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4525748 A	19850625		Method and apparatus for scanning and digitizing	358/2.1	347/3; 358/472;	
19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4493027 A	19850108		Method of performing a call operation in a digital data	712/228	712/243; 712/245	
20	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4455602 A	19840619		Digital data processing system having an I/O means	710/5	710/39; 710/65	
21	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4445177 A	19840424		Digital data processing system utilizing a unique	712/245		
22	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4138737 A	19790206		Non-volatile memory with improved readout	365/78	377/37	

☒ Hts ☒ Details ☐ HTML

Ready NUM

EAST - [-1.wsp:1]

File View Edit Tools Window Help

☐ Pending
☒ Active
 L1: (3776) com
 L2: (23) 1 and
☐ Failed
☐ Saved
☐ Favorites
☒ Tagged (0)

Search:

DB: ☐ Plural
 Default operator: ☒ Highlight all hit terms initially

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020065997 A1	20020530	22	Multi-port memory device and system for addressing the	711/158		
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020064072 A1	20020530		Operable synchronous semiconductor memory device	365/189.05		
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6535150 B1	20030318		Method and apparatus for implementing run-length	341/67		
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6522599 B2	20030218		Operable synchronous semiconductor memory device	365/233	365/230.01	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6507877 B1	20030114		Asynchronous concurrent dual-stream FIFO	710/53		
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6337832 B1	20020108		Operable synchronous semiconductor memory device	365/233	365/230.01	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6334123 B1	20011225		Index relational processor	707/2	707/102; 707/8	
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6291847 B1	20010918		Semiconductor integrated circuit device and process	257/306	257/300	
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6208575 B1	20010327		Dynamic memory array bit line sense amplifier enabled	365/208	365/207	
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5845320 A	19981201		Circuit and method to implement a least recently	711/136	711/128	
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5638071 A	19970610		Efficient architecture for correcting component	341/118	341/120	

Ready NUM

[REDACTED]

EAST - [1.wsp:1]

File View Edit Tools Window Help

(36) (((first adj bitl
(32) (((first adj bitl
(21464) (comparator same
(15819) ((comparator sam
(435) ((comparator same
(435) (((comparator sam
(120) (((comparator sai
(3798) address adi decod

DB: USPAT,US-PGPUB,EPD,JPD,DERWENT,IBM,TD8
Default operator: OR
Highlight all hit terms initially

cell)) and compar\$) and first same second same compar\$) and
first same second same coupled)

BRS form ESR form Image EAT form HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6081036 A	20000627	31	Semiconductor device	257/773	257/295; 257/305;	
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5970007 A	19991019	35	Semiconductor integrated circuit device	365/207	365/203; 365/208	
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5946239 A	19990831	19	Non-volatile semiconductor memory device	365/185.21	365/185.09; 365/185.3	
16	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5943284 A	19990824	40	Semiconductor memory device	365/230.03	365/230.01	
17	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5812148 A	19980922	77	Serial access memory	345/567	345/536	
18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5745402 A	19980428	19	Ferroelectric non-volatile memory	365/145	365/189.01	
19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5740113 A	19980414	22	Semiconductor memory device	365/189.11	365/149; 365/203	
20	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5689461 A	19971118	21	Semiconductor memory device having voltage booster	365/189.11	365/189.07; 365/189.09;	
21	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5671174 A	19970923	22	Ferroelectric memory device	365/145	365/149; 365/203	
22	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5659515 A	19970819	40	Semiconductor memory device capable of refresh operation	365/222	365/230.03; 365/233;	
23	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5559737 A	19960924	16	Nonvolatile semiconductor memory capable of	365/185.25	365/185.2; 365/185.21;	

Ready

NUM

```

(36) (((((first adj bitl
(32) (((((first adj bitl
(21464) (comparator same
(15819) ((comparator sam
(435) ((comparator same
(435) (((comparator sam
(120) (((((comparator sai
(3798) address adi decod

```


DBs	USPAT, US FGPUB, EPD, JPD, DERWENT, IBM, TD8
-----	--

☐ Plurals

Default operator: OR

☒ Highlight all hit terms initially

```
cell) ) and compar$) and first same second same compar$) and
first same second same coupled)
```

 IRS form
 K&R form
 Image
 Text
 HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
23	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5559737 A	19960924	16	Nonvolatile semiconductor memory capable of	365/185.25	365/185.2; 365/185.21;	
24	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5486717 A	19960123	44	SRAM with small planar layout	257/385	257/755; 257/904;	
25	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5485420 A	19960116	15	Static-random-access memory cell and an integrated	365/154	257/277; 257/303;	
26	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5426601 A	19950620	18	Semiconductor memory device having a prolonged data	365/226	365/228; 365/229	
27	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5418750 A	19950523	28	Semiconductor memory device for suppressing noises	365/206	365/149; 365/207;	
28	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5402383 A	19950328	20	Electrically erasable non-volatile semiconductor	365/218	365/185.12; 365/185.23;	
29	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5253210 A	19931012	21	Partitioned bit line structure of EEPROM and	365/185.11	365/185.12; 365/185.21;	
30	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4586171 A	19860429	10	Semiconductor memory	365/63	365/207; 365/208;	
31	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 09147577 A	19970626		Ferroelectric memory device - evaluates data read from			
32	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5559737 A	20010425		Non-volatile semiconductor memory capable of			